













ESD

TVS

TSS

MOV

GDT

PLED







Features

- 150Watts peak pulse power (tp = 8/20µs)
- SLP1610-4 package
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance (Cj=0.3pF typ. IO to IO)
- Protection one data/power line to:
- IEC 61000-4-2 ±15kV contact ±20kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 4A (8/20µs)

Mechanical Data

- SLP1610-4 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

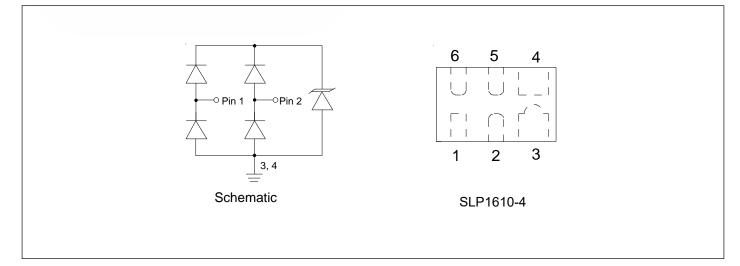
Applications

- Digital Visual Interface (DVI)
- MDDI Ports
- PCI Express
- eSATA Interface

Reference News

SLP1610-4	Marking
	0522

Schematic & PIN Configuration





Absolute Maximum Rating

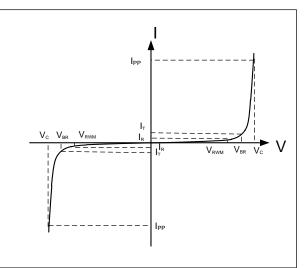
Rating	Symbol	Value	Units
Peak Pulse Power ($t_p = 8/20 \mu s$)	P _{PP}	150	Watts
Peak Pulse Current ($t_p = 8/20 \mu s$) (note1)	I _{pp}	4.0	А
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V _{ESD}	20 15	kV
Lead Soldering Temperature	TL	260(10seconds)	°C
Junction Temperature	TJ	-55 to + 125	°C
Storage Temperature	T _{stg}	-55 to + 125	°C

Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typical	Мах	Units
Reverse Stand-Off Voltage	V _{RWM}				5.0	V
Reverse Breakdown Voltage	V_{BR}	l _⊤ =1mA	6.0			V
Reverse Leakage Current	I _R	V _{RWM} =5V,T=25℃			1.0	μA
Peak Pulse Current	I _{PP}	tp =8/20µs			4.0	А
Clamping Voltage	Vc	I _{PP} =1A,t _p =8/20μs			15	V
Junction Capacitance	Cj	IO to IO V _R = 0V, f = 1MHz		0.3	0.5	pF

Electrical Parameters (TA = 25°C unless otherwise noted)

Symbol	Parameter
I PP	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @ IPP
Vrwm	Working Peak Reverse Voltage
IR	Maximum Reverse Leakage Current @ VRWM
Vbr	Breakdown Voltage @ I⊤
Ιτ	Test Current



Note:. $8/20 \mu s$ pulse waveform.



TypicalCharacteristics

Figure 1: Peak Pulse Power vs. Pulse Time

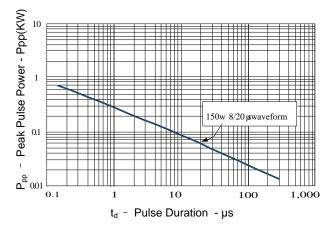


Figure3: Pulse Waveform

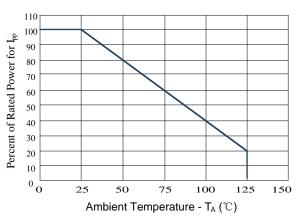
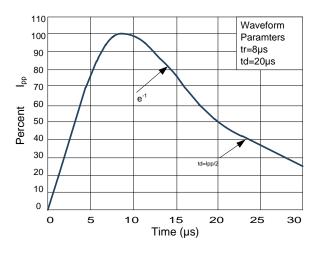
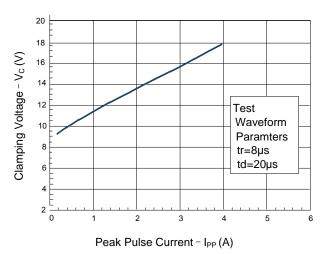


Figure 2: Power Derating Curve

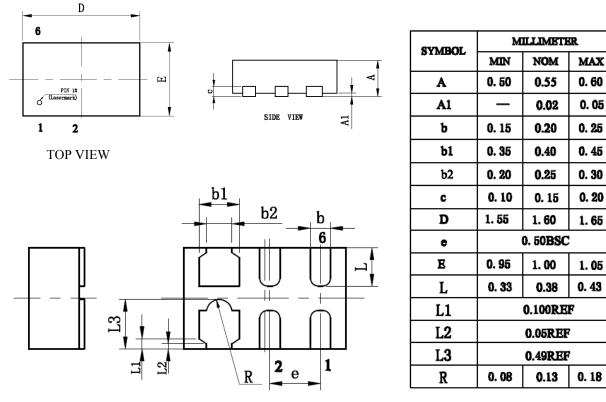
Figure 4: Clamping Voltage vs.lpp







Outline Drawing



BOTTOM VIEW

Order information

Orderable Device	Package	Packing Option
RCLAMP0522P-MS	SLP1610-4	3000PCS



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